

Title (en)

PRODUCTION OF MULTILAYER SEMICONDUCTOR STRUCTURES BY CHANGING THE CARRIER GAS

Title (de)

HERSTELLUNG VON MEHRSCHICHTIGEN HALBLEITERSTRUKTUREN MITTELS TRÄGERGAS-UMSCHALTUNG

Title (fr)

PRODUCTION DE STRUCTURES A SEMI-CONDUCTEUR MULTICOUCHES PAR CHANGEMENT DU GAZ PORTEUR

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Application

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Abstract (en)

[origin: DE19856245A1] The invention relates to a method for producing multilayer semiconductor structures comprised of compound semiconductors by the epitaxy of solid-forming process gases, said process gases being diluted in a carrier gas, on a substrate that is heated for producing the layers. The mixture comprised of the carrier gas and of the process gases is brought into contact with said substrate. In order to produce different layers, the use of different carrier gases, especially hydrogen and nitrogen, is alternated or different mixtures of the carrier gases are used.

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